

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lay bed ON Semiconductor and its officers, employees, ween if such claim alleges that ON Semiconductor was negligent regarding the d



November 2013

RHRP3060 30 A, 600 V Hyperfast Diodes

Features

- Hyperfast Recovery trr = 45 ns (@ I_F = 30 A)
- Max Forward Voltage, VF = 2.1 V (@ Tc = 25°C)
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Ordering Informations

Part Number	Package	Brand
RHRP3060	TO-220AC-2L	RHRP3060

Pin Assignments





The RHRP3060 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast

diodes and is silicon nitride passivated ionimplanted

variety of switching power supplies and other power

switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise

epitaxial planar construction. These devices are intended to be used as freewheeling clamping diodes and diodes in a

in many power switching circuits reducing power loss in the

Description

switching transistors.

1. Cathode 2. Anode

Absolute Maximum Ratings

Symbol	Parameter	RHRP3060	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	600	V	
V _{RWM}	Working Peak Reverse Voltage	600	V	
V _R	DC Blocking Voltage	600	V	
I _{F(AV)}	Average Rectified Forward Current (T _C = 120°C)	30	A	
I _{FRM}	Repetitive Peak Surge Current (Square Wave, 20KHz)	70	А	
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz)	325	А	
P _D	Maximum Power Dissipation	125	W	
E _{AVL}	Avalanche Energy (See Figures 10 and 11)	20	mJ	
T _J , T _{STG}	Operating and Storage Temperature -65 to 175		°C	

Electrical Characteristics	T _C = 25°C unless otherwise noted
-----------------------------------	----------------------------------------------

Symbol	Test Conditions		RHRP3060		
	Test Conditions	Min.	Тур.	Max.	Unit
V _F	I _F = 30 A	-	-	2.1	V
I _F = 30 A, T _C = 150°C		-	-	1.7	V
I _R	V _R = 400 V		-	-	μA
	V _R = 600 V	-	-	250	μA
	V _R = 400 V, T _C = 150°C	-	-	-	mA
	V _R = 600 V, T _C = 150°C	-	-	1.0	mA
t _{rr}	I _F = 1 A, dI _F /dt = 200 A/μs	-	-	40	ns
	I _F = 30 A, dI _F /dt = 200 A/μs	-	-	45	ns
t _a	I _F = 30 A, dI _F /dt = 200 A/μs	-	22	-	ns
t _b	I _F = 30 A, dI _F /dt = 200 A/μs	-	18	-	ns
Q _{RR}	I _F = 30 A, dI _F /dt = 200 A/μs	-	100	-	nC
CJ	V _R = 600 V, I _F = 0 A	-	85	-	pF
R _{0JC}		-	-	1.2	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 $\mu s,$ D = 2%)

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 9), summation of t_a + t_b .

 t_a = Time to reach peak reverse current (See Figure 9).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

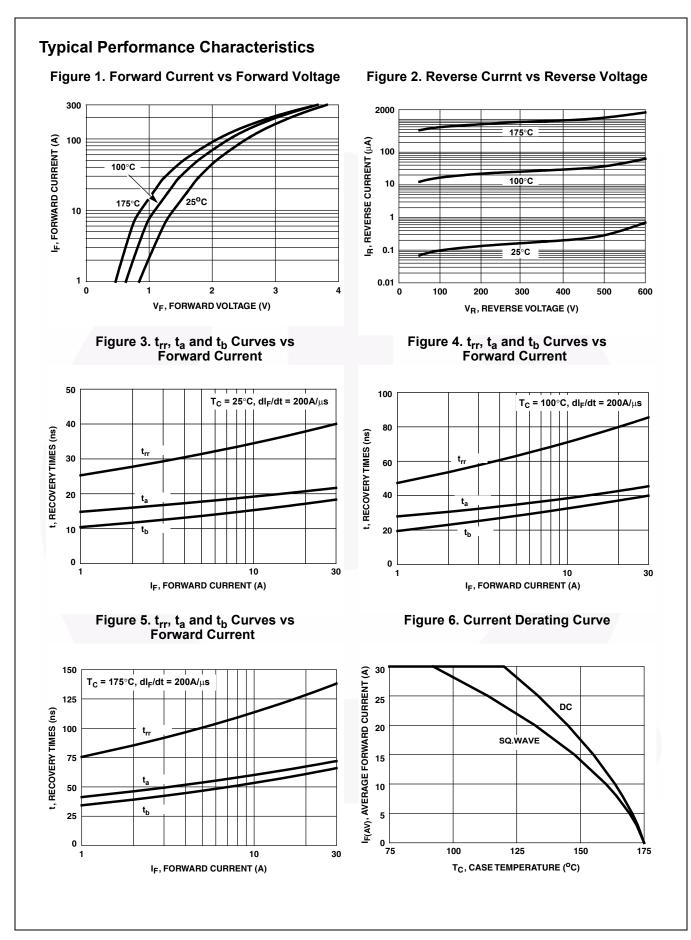
Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

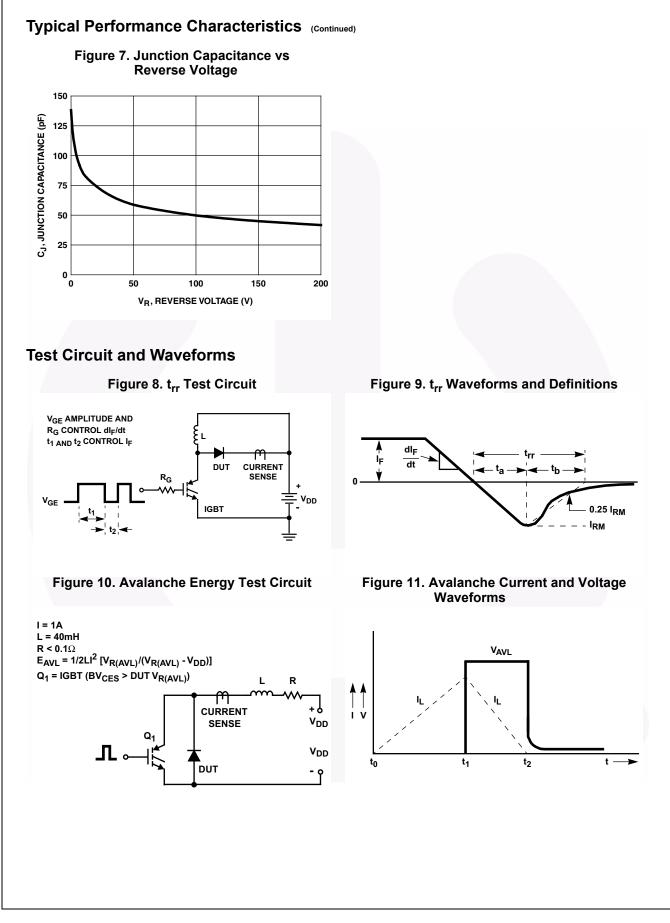
 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = Duty cycle.



3



RHRP3060 — Hyperfast Diode

Ø 4.09 3.50 ⊕ 0.36 M B A M 10.67 В Α 9.65 8.89 3.43 1.40 6.86 2.54 0.51 6.86 **7**° 5.84 3° T 13.40 16.51 12,19 14,22 16.15 9.40 15,75 8.38 **5**° **5°** 3° 3° 6.35 MAX 2 1 0.60 MAX С 14.73 13,60 1.65 (1.91)1.25 F Т 0.61 2.54 0.33 1.02 2.92 0.38 2.03 5.08 ⊕ 0.36 M C A B **5° 5°** 3° 3° -...... FAIRCHILD ... 4.80 4.30

NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DRAWING FILE NAME: TO220A02REV5



* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT <u>HTTP://WWW.FAIRCHILDSEMI.COM</u>, FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms			
Datasheet Identification	Product Status	Definition	
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.	
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.	
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.	
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.	

Rev. 177